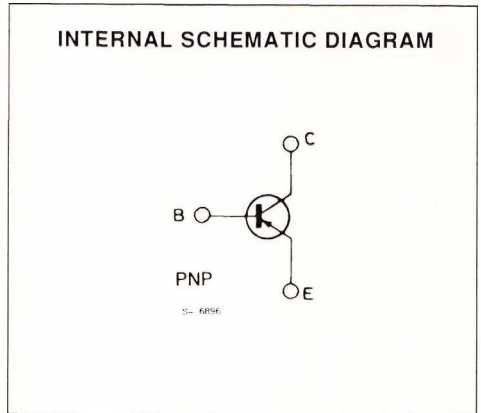
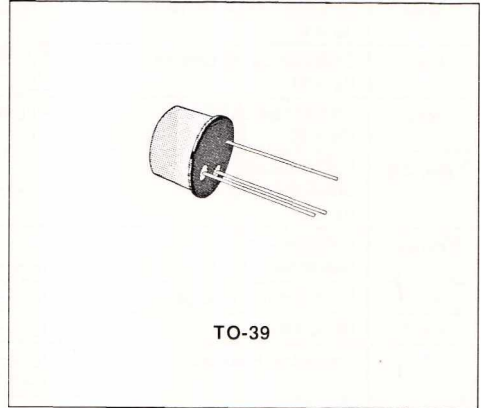


HIGH-VOLTAGE AMPLIFIER

DESCRIPTION

The 2N5415S is a silicon planar epitaxial PNP transistor in Jedec TO-39 metal case, intended for high voltage switching and linear amplifier applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	- 200	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	- 200	V
V_{EB0}	Emitter-base Voltage ($I_C = 0$)	- 4	V
I_{CM}	Collector Peak Current	- 1	A
P_{tot}	Total Power Dissipation at $T_{amb} \leq 25^\circ C$ at $T_{case} \leq 25^\circ C$	1	W
		10	W
T_{stg}, T_j	Storage and Junction Temperature	- 55 to 200	$^\circ C$

THERMAL DATA

$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	17.5	$^{\circ}C/W$
$R_{th\ j-amb}$	Thermal Resistance Junction-ambient	Max	175	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = -175\ V$			-50	μA
I_{CEO}	Collector Cutoff Current ($I_B = 0$)	$V_{CE} = -150\ V$			-50	μA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = -4\ V$			-20	μA
$V_{(BR)CEO}^*$	Collector-emitter Breakdown Voltage ($I_B = 0$)	$I_C = -2\ mA$	-200			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = -50\ mA$ $I_B = -5\ mA$			-2.5	V
V_{BE}^*	Base-Emitter Voltage	$I_C = -50\ mA$ $V_{CE} = -10\ V$			-1.5	V
h_{FE}^*	DC Current Gain	$I_C = -50\ mA$ $V_{CE} = -10\ V$	30		150	
f_T	Transition Frequency	$I_C = -10\ mA$ $V_{CE} = -10\ V$ $f = 5\ MHz$	15			MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $V_{CB} = -10\ V$ $f = 1\ MHz$			15	pF

* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.